

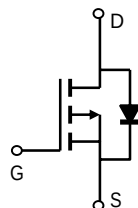
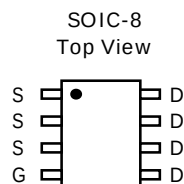
AO4449
P-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4449 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO4449 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

$V_{DS} (V) = -30V$
 $I_D = -7 A (V_{GS} = -10V)$
 $R_{DS(ON)} < 34m\Omega (V_{GS} = -10V)$
 $R_{DS(ON)} < 54m\Omega (V_{GS} = -4.5V)$


Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^F	I_D	-7	A
$T_A=25^\circ C$		-4.6	
Pulsed Drain Current ^B	I_{DM}	-40	
Power Dissipation ^A	P_D	3.1	W
		2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ C/W$
$t \leq 10s$		60	75	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	60	75	$^\circ C/W$
Steady-State		16	24	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-2	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-40			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-7A T _J =125°C		27 38	34	mΩ
		V _{GS} =-4.5V, I _D =-5A		43	54	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-7A		15		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.77	-1	V
I _S	Maximum Body-Diode Continuous Current				-3.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		980	1225	pF
C _{oss}	Output Capacitance			150		pF
C _{rss}	Reverse Transfer Capacitance			115		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.2	3.3	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-15V, I _D =-7A		18.7	24	nC
Q _{g(4.5V)}	Total Gate Charge (4.5V)			9.6		nC
Q _{gs}	Gate Source Charge			3.2		nC
Q _{gd}	Gate Drain Charge			4.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =2.2Ω, R _{GEN} =3Ω		7.7		ns
t _r	Turn-On Rise Time			6		ns
t _{D(off)}	Turn-Off DelayTime			20		ns
t _f	Turn-Off Fall Time			7		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-7A, dI/dt=100A/μs		21	26	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-7A, dI/dt=100A/μs		13		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s thermal resistance rating.

Rev0: Dec 2006

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

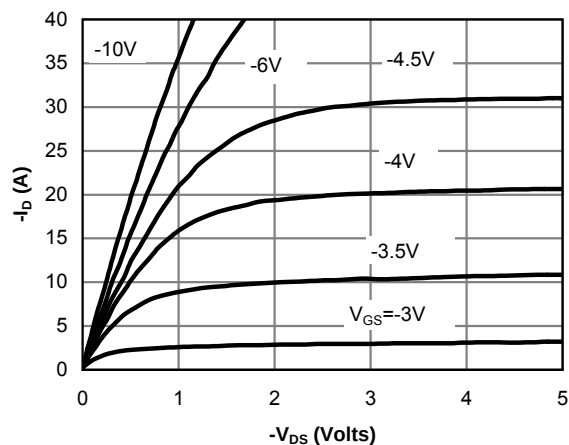


Figure 1: On-Region Characteristics

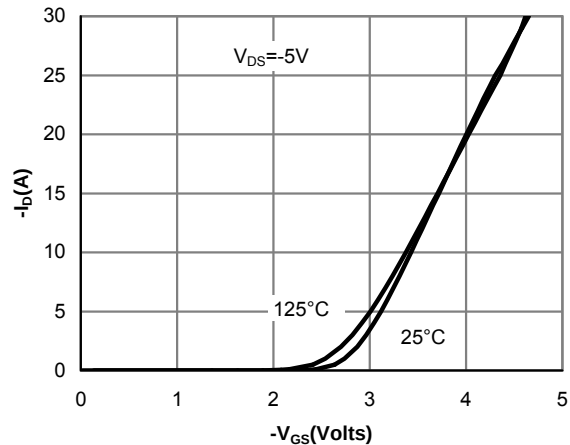


Figure 2: Transfer Characteristics

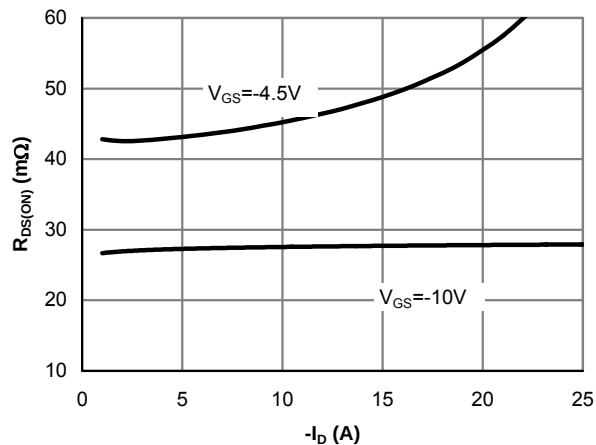


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

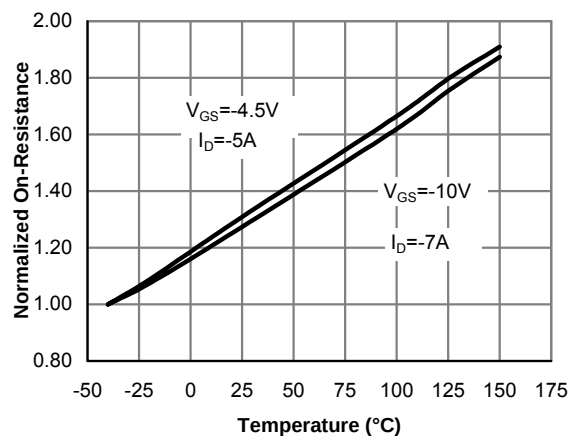


Figure 4: On-Resistance vs. Junction Temperature

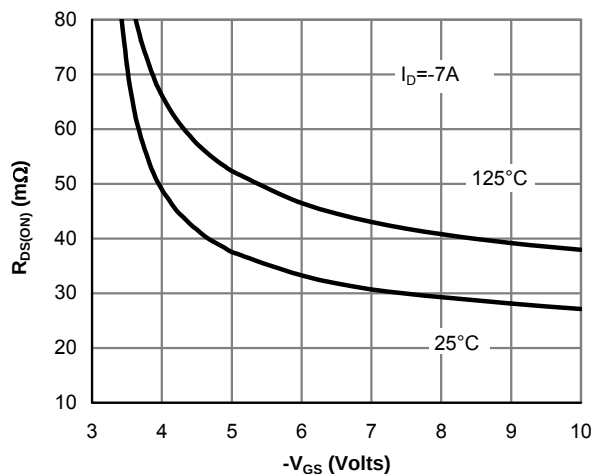


Figure 5: On-Resistance vs. Gate-Source Voltage

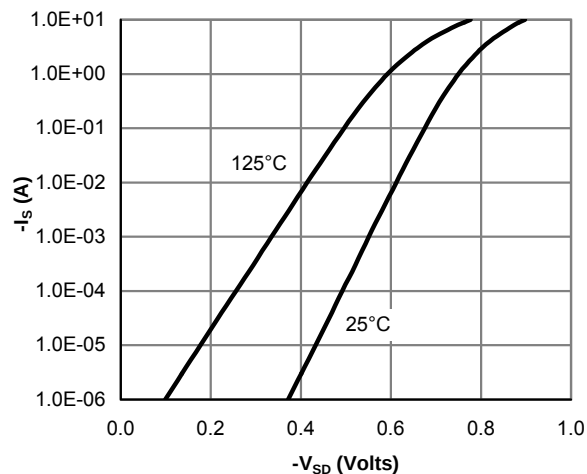


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

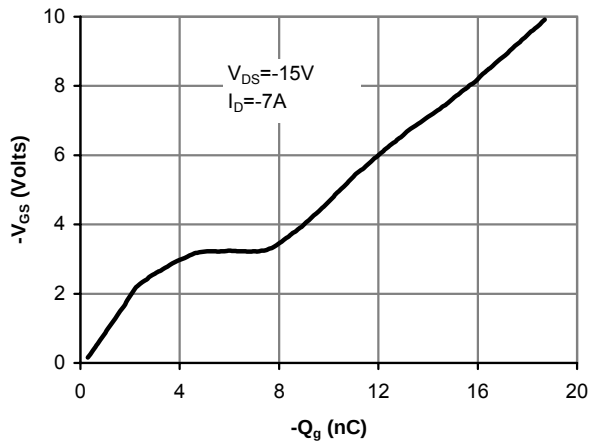


Figure 7: Gate-Charge Characteristics

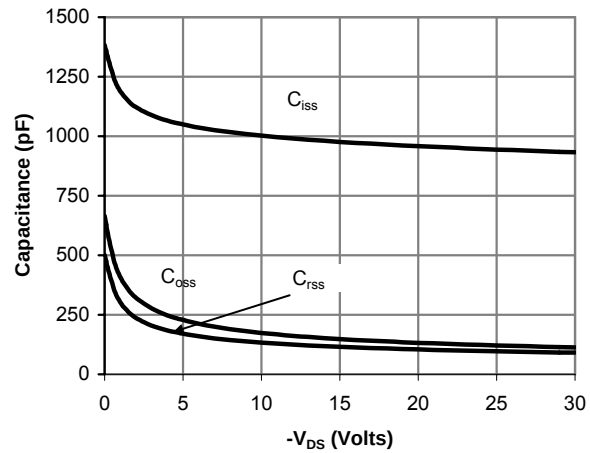


Figure 8: Capacitance Characteristics

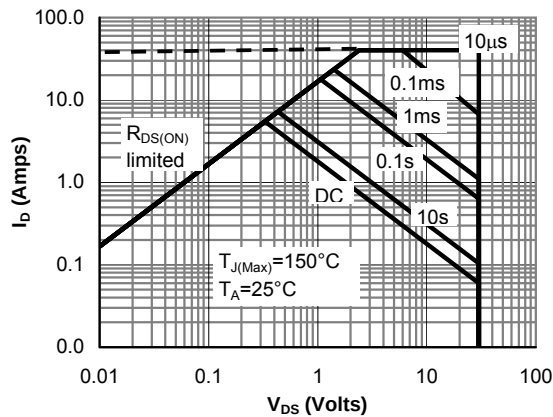


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

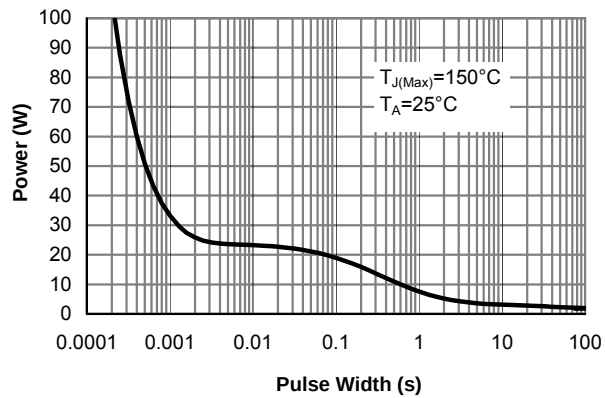


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

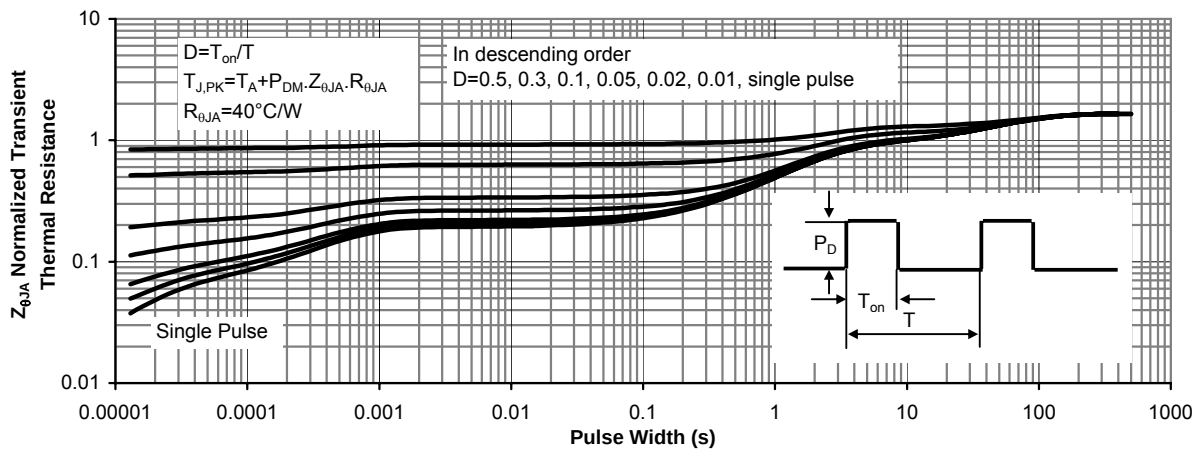


Figure 11: Normalized Maximum Transient Thermal Impedance